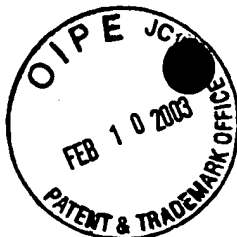


1201.63407



PATENT

#22/Supp.
I.D.S.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

2/20/03

Applicants: Nayfeh et al.

Serial No.: 09/496,506

Filed: February 2, 2000

For: SILICON NANOPARTICLE
FIELD EFFECT TRANSISTOR AND
TRANSISTOR MEMORY DEVICE

Art Unit: 2811

Examiner: Crane, S.

) I hereby certify that this paper is being deposited with
) the United States Postal Service as FIRST-CLASS mail
) in an envelope addressed to: Assistant Commissioner
) for Patents, Washington, D.C. 20231, on this date

) Feb 5, 2003

) Date
) F-CLASS WCM

) Appr. February 20, 1998

As P. R.
Registration No. 43,874

Attorney for Applicant

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In accordance with 37 C.F.R. §§1.56, 1.97 and 1.98, Applicants through
counsel herewith:

Submit a copy of the patents and publications set forth in the attached form
PTO-1449 as follows:

U.S. PATENT DOCUMENTS

PATENT NO.	PATENTEE	ISSUE DATE
3,597,624	David Weiner et al.	08/03/1971
5,537,000	Alivisatos et al.	07/16/1996

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PATENT NO.	PATENTEE	ISSUE DATE
5,881,200	Burt	03/09/1999
5,906,670	Dobson et al.	05/25/1999
6,326,311	Ueda et al.	12/04/2001

FOREIGN PATENT DOCUMENTS

DOCUMENT NO.	PUBLICATION DATE	COUNTRY
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0 354 141	02/07/1990	EP
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Shoutian Li, I.N. Germanenko, M.S. El Shall, "Semiconductor nanoparticles in contact: quenching of the photoluminescence from silicon nanocrystals by WO₃ nanoparticles suspended in solution", Journal of Physical Chemistry B, Vol. 102, No. 38, pp. 7319-7322, Sept. 17, 1998 (Abstract).

Tetsuya Makimura, Yasuhiko Kunii and Kouichi Murakami, "Light Emission from Nanometer-Sized Silicon Particles Fabricated by the Laser Ablation Method", Jpn. J. Appl. Phys., Vol. 35, (1996), pp. 4780-4784.

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L.E. Brus, P.F. Szajowski, W.L. Wilson, T.D. Harris, S. Schuppler, and P.H. Citrin, "Electronic Spectroscopy and Photophysics of Si Nanocrystals: Relationship to Bulk c-Si and Porous Si", J. Am. Chem. Soc., 1995, Vol. 117, pp. 2915-2922.

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Gennadiy Belomoin, Joel Therrien, and Munir Nayfeh, "Oxide and hydrogen capped ultrasmall blue luminescent Si nanoparticles", Applied Physics Letters, Volume 77, Number 6, 7 August 2000, pp. 779-780.

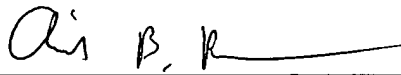
REMARKS

Applicants respectfully request that the Examiner consider the above-listed references in the examination of this application and list these references of record in the application.

Respectfully submitted,

GREER, BURNS & CRAIN, LTD.

Date: February 5, 2003

By: 
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